

IN THE SPECIFICATION:

Please amend paragraph [0067] as follows:

[0067] Figure 9(B) illustrates a preferred method of forming a bipolar transistor, according to the present invention. The method comprises forming 910 a collector region 15 in a wafer. Next, an epitaxial layer 5, 6 is grown 915 on the wafer. The epitaxial layer comprises carbon, and has a semiconductor region 5 above the collector region 15. Then, an emitter 17 is formed 920 on the semiconductor region 5, wherein the emitter 17 includes an insulator portion 10, 11. Finally, the semiconductor region 5 is doped 925 in sufficient quantities to reduce the resistance of the semiconductor 5 to less than approximately 4 Kohms/cm². The step of doping 925 provides the dopant in peak concentration of approximately 1×10^{20} per cm³ to 1×10^{21} per cm³. As mentioned, the carbon limits the outdiffusion of the dopant within the semiconductor region 5. Moreover, the dopant comprises one of boron, aluminum, gallium, indium, and titanium. Also, as mentioned, the semiconductor region 5, 6 comprises silicon germanium. Additionally, the carbon maintains the dopant within a central portion of the semiconductor region 5, 6, which is best seen in Figure 12. Finally, the step 915 of growing the epitaxial layer includes growing a material including a concentration of carbon which is less than approximately 3%.

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